



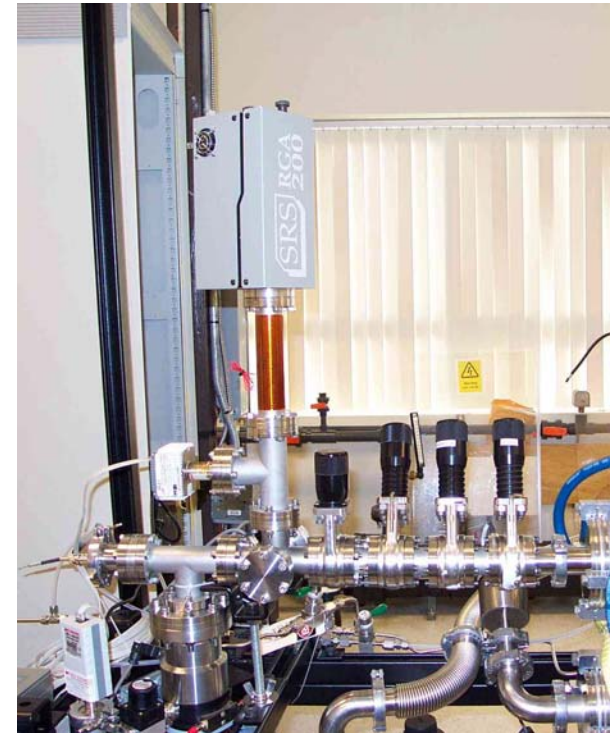
# IEUVI Resist Technical Working Group

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# Experimental set-up

- Outgassing measurements were performed using a 200 amu residual gas analyser (RGA / QMS).
- The pumping speed at the chamber was approximately 15 l/s.
- The system base pressure was better than  $1 \times 10^{-8}$  Torr, rising to  $5 \times 10^{-7}$  Torr during exposure. The practical sensitivity limit of the RGA was  $1 \times 10^{-12}$  Torr.
- The wafer samples were positioned 90cm from the plasma, at an angle of incidence  $45^\circ$  to both the EUV beam and the RGA.
- Exposures typically performed with the sample under vacuum for 1 hour before exposing, although longer time (+24 hours) also investigated.



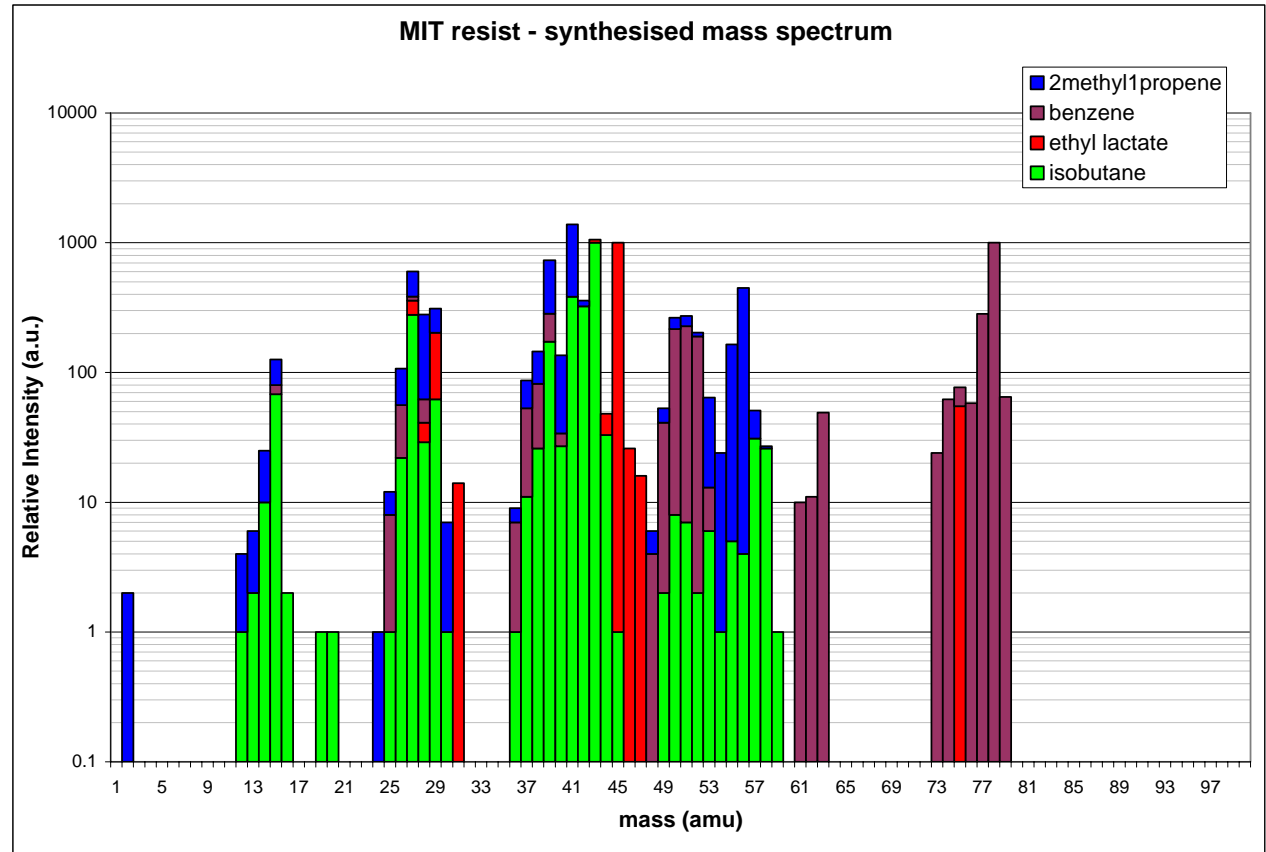
# Exposure Conditions

- Measurements were performed using EUV light from an electrodeless z-pinch gas discharge source.
- Exposure conditions:
- For the low power exposures a dose of  $1\text{mJ}/\text{cm}^2$  is reached in approximately 87 seconds exposure.
- For the high power exposures a dose of  $1\text{mJ}/\text{cm}^2$  is reached in approximately 1 second exposure.
  - High power exposure is achieved through burst mode operation, 2 second burst with 20% duty cycle.
- EUV light was filtered by a 200nm thick zirconium foil, size  $1\text{cm}^2$ , resulting in an exposure area at the sample of  $0.5\text{cm}^2$



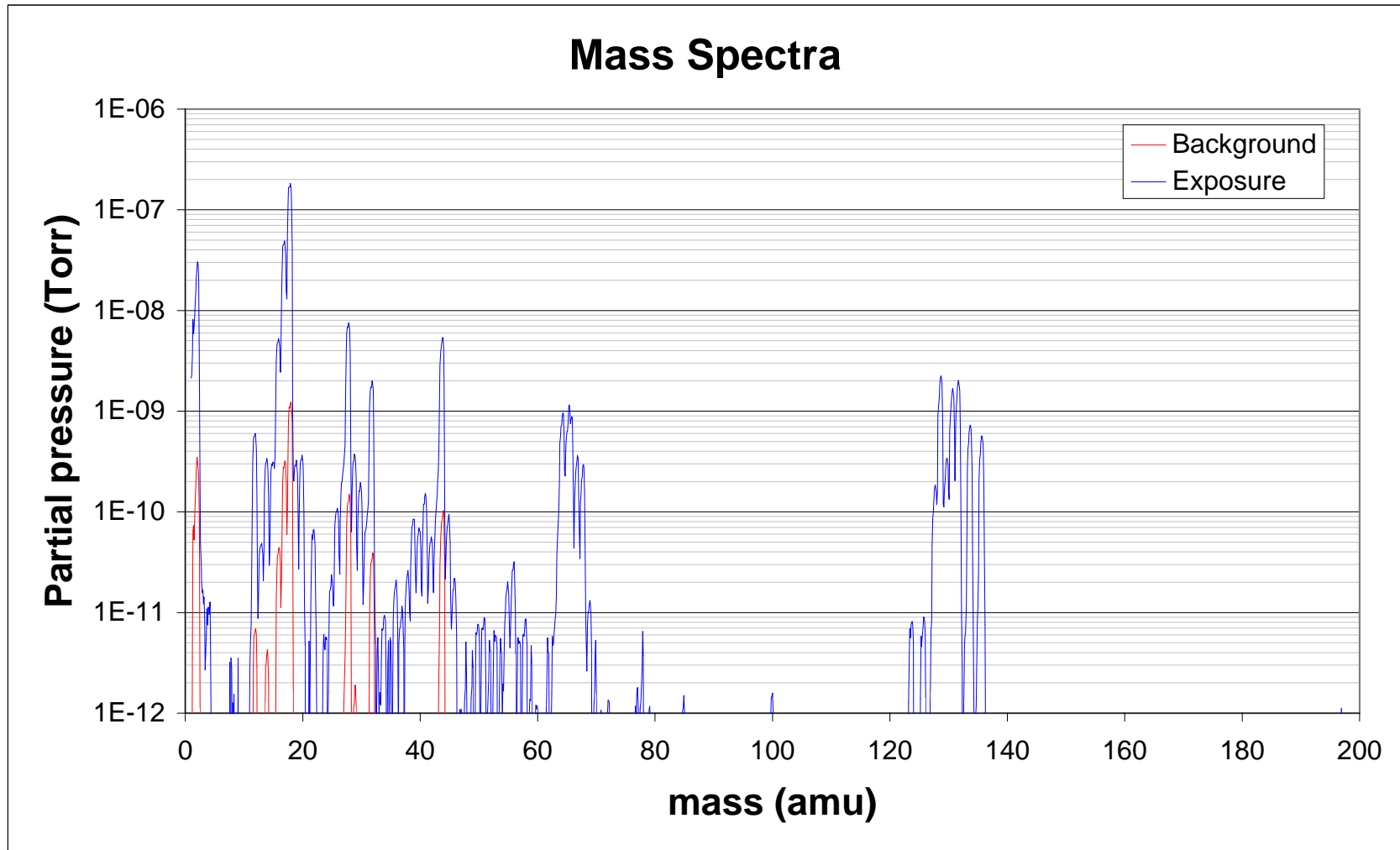
# Photo-Resist Details

- > 2 methyl-1-propene
  - Parent ion at 56amu
  - Dominant species 41amu
- > Benzene
  - Parent ion at 78amu
  - Dominant species 77amu
- > Isobutane
  - Parent ion at 58amu
  - Dominant species 43amu
- > Ethyl lactate (solvent)
  - Parent ion at 118amu
  - Dominant species 45amu

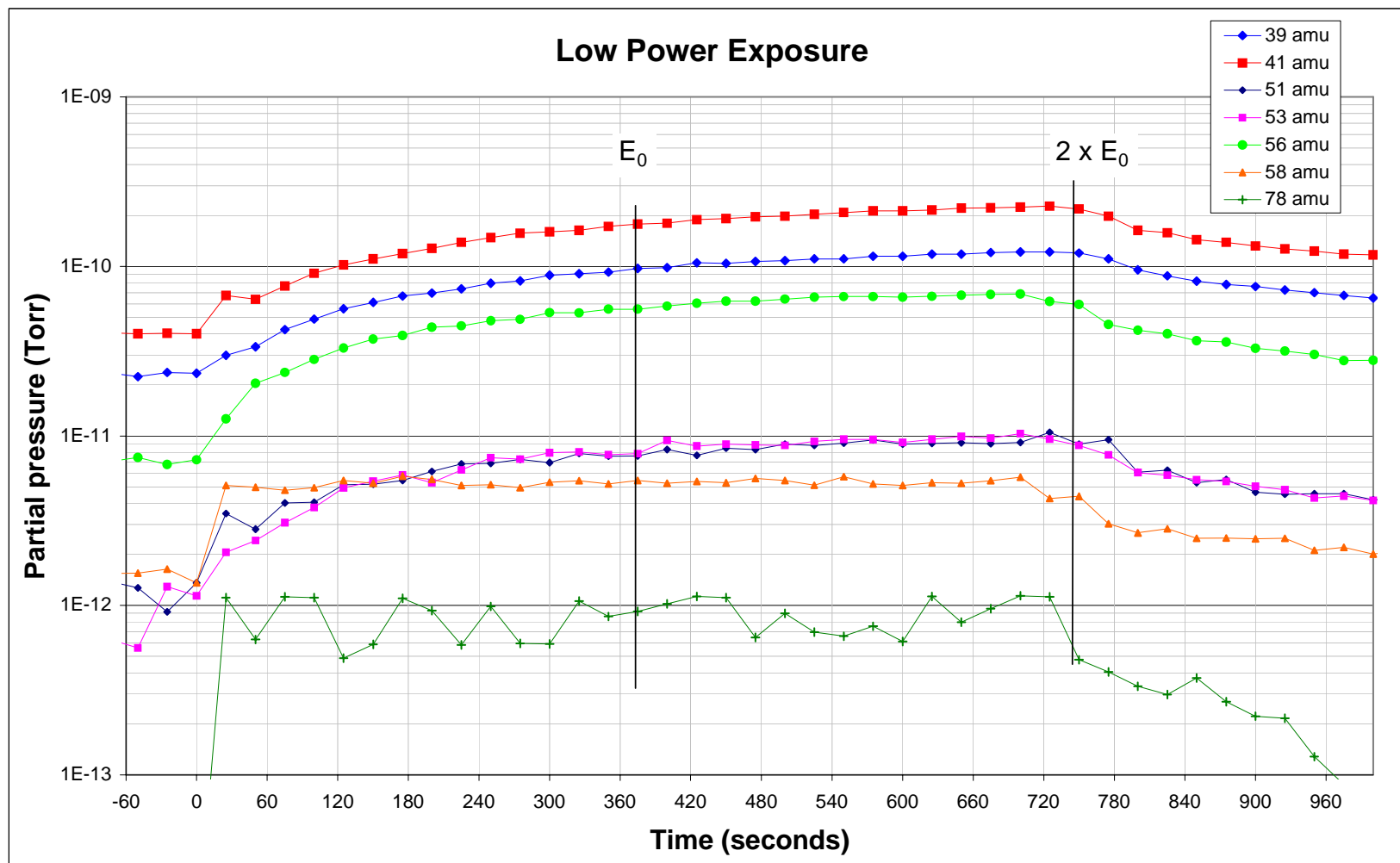


- > Exposure dose to clear resist  $4\text{mJ}/\text{cm}^2$

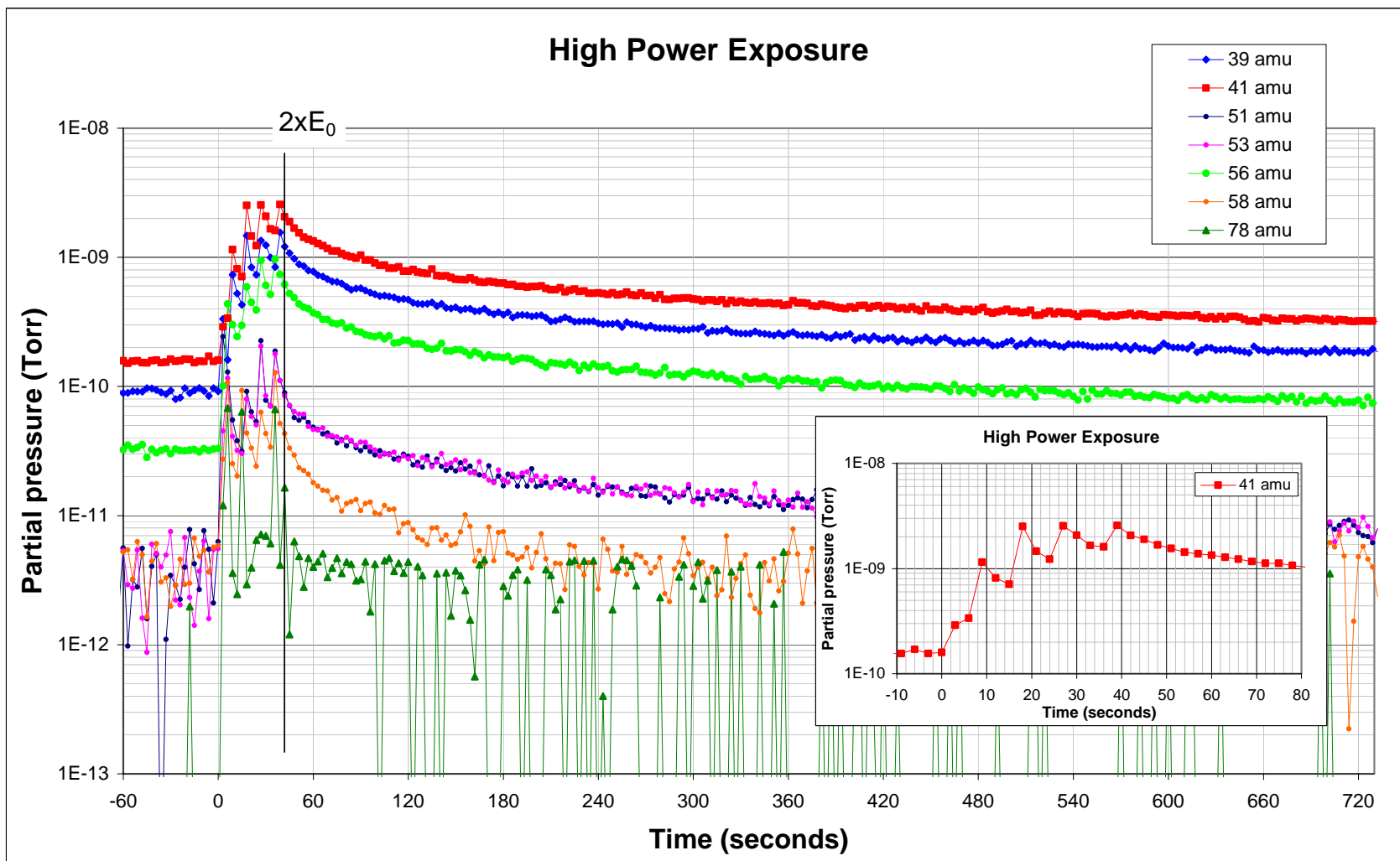
# Limitations of RGA



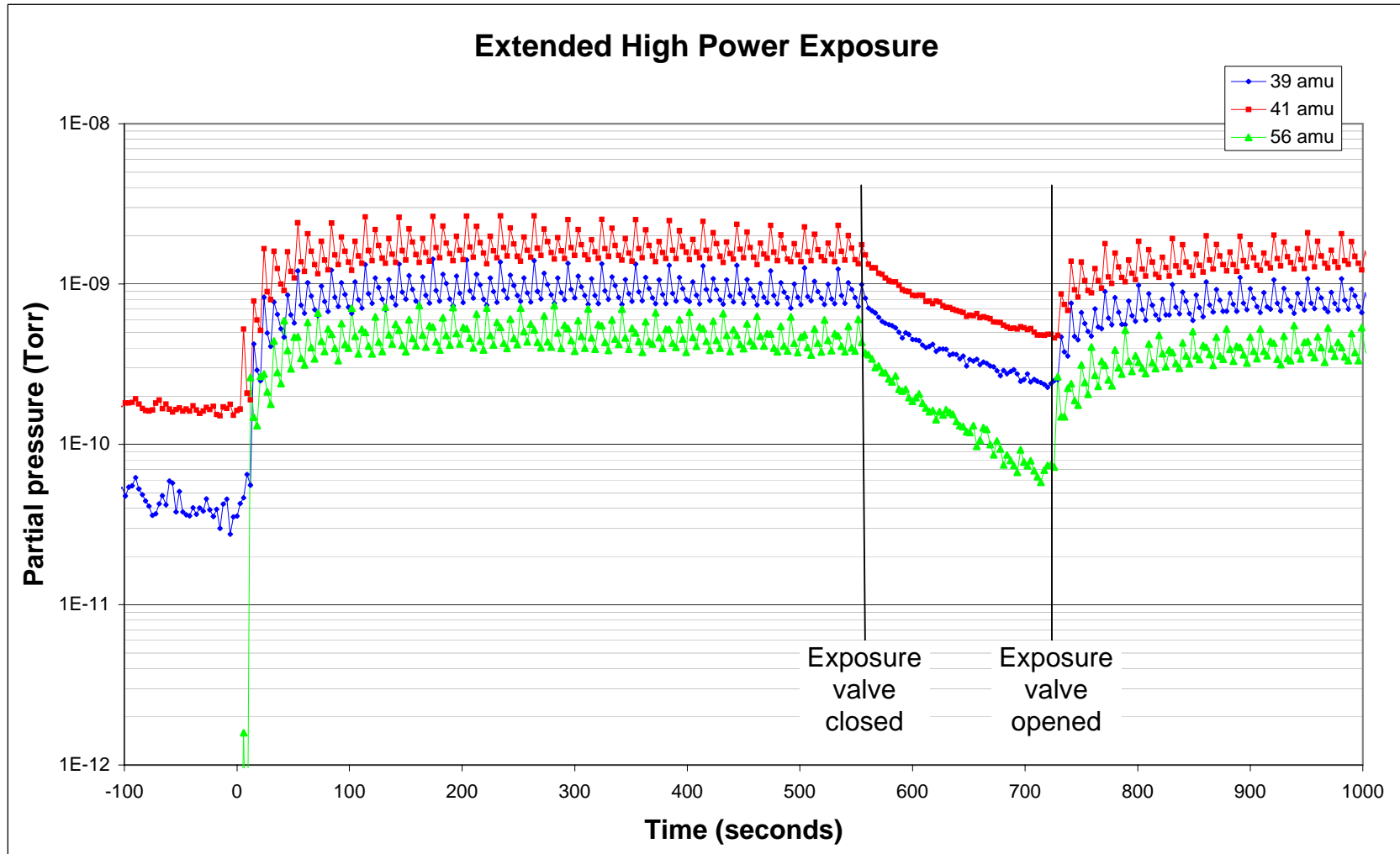
# Low Power Exposure



# High Power Exposure



# Extended High Power Exposure





# Preliminary Conclusions

- Specific outgassing has been observed at 39, 41, 43, 51, 53, 56, 78amu under exposure conditions where the sample is under vacuum for a short period of time before measuring, approximately 1 hour.
  - 39, 41 and 56amu are likely from of 2-methyl-1-propene
  - 78amu is characteristic of Benzene
  - 58amu is evidence of isobutane.
- The outgassing rate (partial pressure level) is observed to increase by approximately one decade from 'low' to 'high' power exposure conditions.
- Extended 'high' power exposure displays no significant increase, or decrease, in outgassing rate as a function of time (during the term of the experiment).
- Possible dependence on time under vacuum before exposing and measuring.
  - During one series of measurements the sample remained under vacuum for 30 hours before exposure and in this case there was no observable outgassing above 56amu.